



# **SNS COLLEGE OF TECHNOLOGY**

## **Coimbatore-35**

### **An Autonomous Institution**



Accredited by NBA – AICTE and Accredited by NAAC – UGC with ‘A++’(III Cycle) Grade  
Approved by AICTE, New Delhi & Affiliated to Anna University, Chennai

## **DEPARTMENT OF ELECTRONICS & COMMUNICATION ENGINEERING**

### **23ECB101 – CIRCUIT ANALYSIS AND DEVICES**

I YEAR/ II SEMESTER

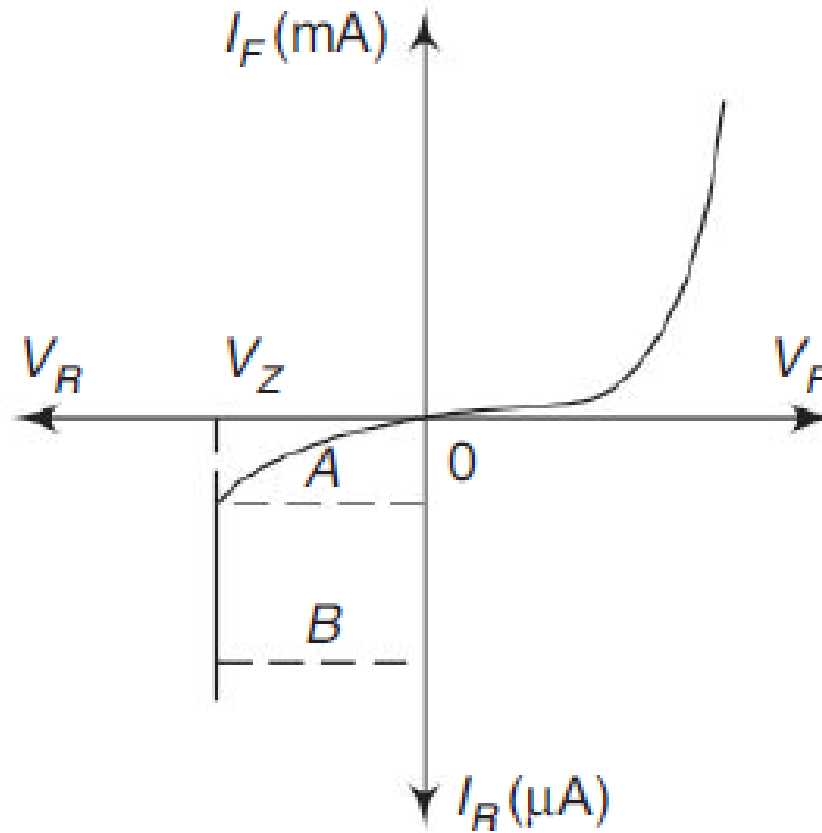
#### **UNIT 4 – SEMICONDUCTOR DIODES AND THEIR APPLICATIONS**

##### **TOPIC - Zener and Avalanche Breakdown**



# Introduction

- When the reverse voltage reaches breakdown voltage in a normal PN junction diode, the current through the junction and the power dissipated at the junction will be high.
- Such an operation is destructive and the diode gets damaged.
- Whereas diodes can be designed with adequate power dissipation capabilities to operate in the breakdown region.
- One such diode is known as the Zener diode.
- The Zener diode is heavily doped than the ordinary diode.



*V-I characteristics of a Zener diode*



- From the  $V-I$  characteristics of the Zener diode, shown in Figure, it is found that the operation of the Zener diode is same as that of an ordinary PN diode under forward-biased condition.
- Whereas under reverse-biased condition, breakdown of the junction occurs.
- The breakdown voltage depends upon the amount of doping.
- If the diode is heavily doped, the depletion layer will be thin and, consequently, breakdown occurs at lower reverse voltage and further, the breakdown voltage is sharp.



- Whereas a lightly doped diode has a higher breakdown voltage. Thus, breakdown voltage can be selected with the amount of doping.
- The sharp increasing currents under breakdown conditions are due to the following two mechanisms.

Avalanche breakdown  
Zener breakdown



# Avalanche breakdown



- As the applied reverse bias increases, the field across the junction increases correspondingly.
- Thermally generated carriers, while traversing the junction, acquire a large amount of kinetic energy from this field.
- As a result, the velocity of these carriers increases. These electrons disrupt covalent bond by colliding with immobile ions and create new electron-hole pairs.
- These new carriers again acquire sufficient energy from the field and collide with other immobile ions thereby generating further electron-hole pairs.
- This process is cumulative in nature and results in generation of avalanche of charge carriers within a short time.



- This mechanism of carrier generation is known as **avalanche multiplication**.
- This process results in flow of large amount of current at the same value of reverse bias.



# Zener Breakdown



- When the P- and N-regions are heavily doped, direct rupture of covalent bonds takes place because of the strong electric fields, at the junction of the PN diode.
- The new electron-hole pairs so created increase the reverse current in a reverse-biased PN diode.
- The increase in current takes place at a constant value of reverse bias typically below 6 V for heavily doped diodes.
- As a result of heavy doping of P- and N-regions, the depletion-region width becomes very small and for an applied voltage of 6 V or less, the field across the depletion region becomes very high, of the order of  $10^7$  V/m, making conditions suitable for Zener breakdown.





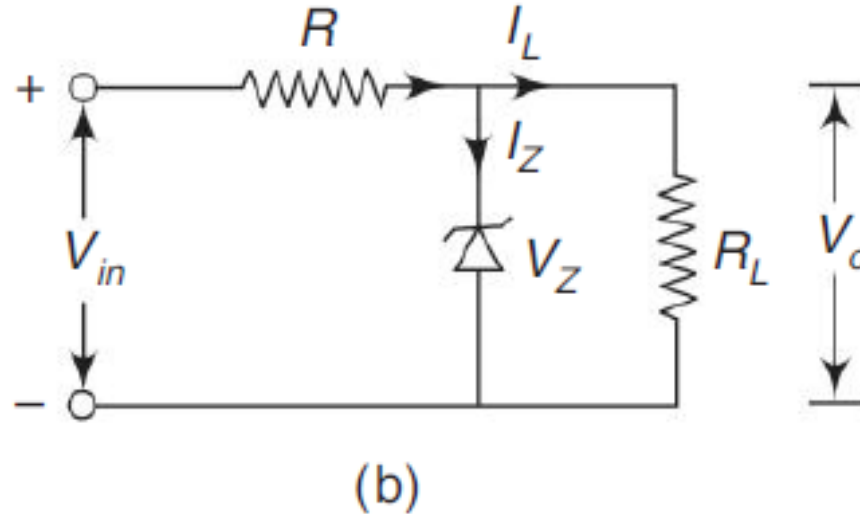
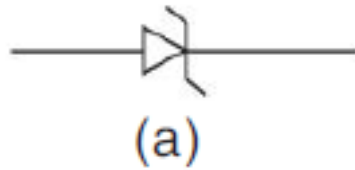
- For lightly doped diodes, Zener breakdown voltage becomes high and breakdown is then predominantly by avalanche multiplication.
- Though Zener breakdown occurs for lower breakdown voltage and avalanche breakdown occurs for higher breakdown voltage, such diodes are normally called Zener diodes.



# Zener Diode Applications



- From the Zener characteristics, under the reverse-bias condition, the voltage across the diode remains almost constant although the current through the diode increases as shown in region AB.
- Thus, the voltage across the Zener diode serves as a reference voltage.
- Hence, the diode can be used as a voltage regulator.
- In Figure, it is required to provide constant voltage across load resistance  $R_L$ , whereas the input voltage may be varying over a range.



*Zener diode: (a) Circuit symbol (b) As a voltage regulator*

- As shown, Zener diode is reverse biased and as long as the input voltage does not fall below  $V_Z$  (Zener breakdown voltage), the voltage across the diode will be constant and hence the load voltage will also be constant.

